

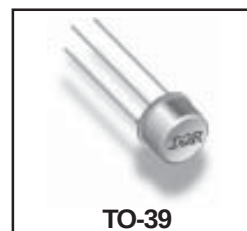
**RADIATION HARDENED
POWER MOSFET
THRU-HOLE (TO-39)**

**IRHF57230SE
JANSR2N7498T2
200V, N CHANNEL
REF:MIL-PRF-19500/706**

R5™ TECHNOLOGY

Product Summary

Part Number	Radiation Level	R _{DS(on)}	I _D	QPL Part Number
IRHF57230SE	100K Rads (Si)	0.24Ω	7.0A	JANSR2N7498T2



International Rectifier's R5™ technology provides high performance power MOSFETs for space applications. These devices have been characterized for Single Event Effects (SEE) with useful performance up to an LET of 80 (MeV/(mg/cm²)). The combination of low R_{DS(on)} and low gate charge reduces the power losses in switching applications such as DC to DC converters and motor control. These devices retain all of the well established advantages of MOSFETs such as voltage control, fast switching, ease of paralleling and temperature stability of electrical parameters.

Features:

- Single Event Effect (SEE) Hardened
- Ultra Low R_{DS(on)}
- Neutron Tolerant
- Identical Pre- and Post-Electrical Test Conditions
- Repetitive Avalanche Ratings
- Dynamic dv/dt Ratings
- Simple Drive Requirements
- Ease of Paralleling
- Hermetically Sealed

Absolute Maximum Ratings

Pre-Irradiation

	Parameter		Units
I _D @ V _{GS} = 12V, T _C = 25°C	Continuous Drain Current	7.0	A
I _D @ V _{GS} = 12V, T _C = 100°C	Continuous Drain Current	4.5	
I _{DM}	Pulsed Drain Current ①	28	
P _D @ T _C = 25°C	Max. Power Dissipation	25	W
	Linear Derating Factor	0.2	W/°C
V _{GS}	Gate-to-Source Voltage	±20	V
E _{AS}	Single Pulse Avalanche Energy ②	130	mJ
I _{AR}	Avalanche Current ①	7.0	A
E _{AR}	Repetitive Avalanche Energy ①	2.5	mJ
dv/dt	Peak Diode Recovery dv/dt ③	4.2	V/ns
T _J	Operating Junction	-55 to 150	°C
T _{STG}	Storage Temperature Range		
	Lead Temperature	300 (0.063 in./1.6mm from case for 10s)	
	Weight	0.98 (Typical)	g

For footnotes refer to the last page

Electrical Characteristics @ T_j = 25°C (Unless Otherwise Specified)

	Parameter	Min	Typ	Max	Units	Test Conditions
BV _{DSS}	Drain-to-Source Breakdown Voltage	200	—	—	V	V _{GS} = 0V, I _D = 1.0mA
ΔBV _{DSS} /ΔT _j	Temperature Coefficient of Breakdown Voltage	—	0.26	—	V/°C	Reference to 25°C, I _D = 1.0mA
R _{DS(on)}	Static Drain-to-Source On-State Resistance	—	—	0.24	Ω	V _{GS} = 12V, I _D = 4.5A ④
V _{GS(th)}	Gate Threshold Voltage	2.5	—	4.5	V	V _{DS} = V _{GS} , I _D = 1.0mA
g _{fs}	Forward Transconductance	4.2	—	—	S (Ω)	V _{DS} > 15V, I _{DS} = 4.5A ④
I _{DSS}	Zero Gate Voltage Drain Current	—	—	10	μA	V _{DS} = 160V, V _{GS} = 0V
		—	—	25		V _{DS} = 160V, V _{GS} = 0V, T _j = 125°C
I _{GSS}	Gate-to-Source Leakage Forward	—	—	100	nA	V _{GS} = 20V
I _{GSS}	Gate-to-Source Leakage Reverse	—	—	-100		V _{GS} = -20V
Q _g	Total Gate Charge	—	—	47	nC	V _{GS} = 12V, I _D = 7.0A V _{DS} = 100V
Q _{gs}	Gate-to-Source Charge	—	—	12		
Q _{gd}	Gate-to-Drain ('Miller') Charge	—	—	16		
t _{d(on)}	Turn-On Delay Time	—	—	25	ns	V _{DD} = 100V, I _D = 7.0A V _{GS} = 12V, R _G = 7.5Ω
t _r	Rise Time	—	—	100		
t _{d(off)}	Turn-Off Delay Time	—	—	35		
t _f	Fall Time	—	—	40		
L _S + L _D	Total Inductance	—	7.0	—	nH	Measured from Drain lead (6mm /0.25in. from package) to Source lead (6mm /0.25in. from package) with Source wires internally bonded from Source Pin to Drain Pad
C _{iss}	Input Capacitance	—	1014	—	pF	V _{GS} = 0V, V _{DS} = 25V f = 1.0MHz
C _{oss}	Output Capacitance	—	182	—		
C _{rss}	Reverse Transfer Capacitance	—	8.8	—		

Source-Drain Diode Ratings and Characteristics

	Parameter	Min	Typ	Max	Units	Test Conditions
I _S	Continuous Source Current (Body Diode)	—	—	7.0	A	T _J = 25°C, I _S = 7.0A, V _{GS} = 0V ④
I _{SM}	Pulse Source Current (Body Diode) ①	—	—	28		
V _{SD}	Diode Forward Voltage	—	—	1.5	V	T _J = 25°C, I _F = 7.0A, di/dt ≤ 100A/μs V _{DD} ≤ 25V ④
t _{rr}	Reverse Recovery Time	—	—	274	ns	
Q _{RR}	Reverse Recovery Charge	—	—	2.2	μC	
t _{on}	Forward Turn-On Time	Intrinsic turn-on time is negligible. Turn-on speed is substantially controlled by L _S + L _D .				

Thermal Resistance

	Parameter	Min	Typ	Max	Units	Test Conditions
R _{thJC}	Junction-to-Case	—	—	5.0	°C/W	
R _{thJA}	Junction-to-Ambient	—	175	—		Typical socket mount

Note: Corresponding Spice and Saber models are available on the International Rectifier Website.

For footnotes refer to the last page

Radiation Characteristics

IRHF57230SE, JANSR2N7498T2

International Rectifier Radiation Hardened MOSFETs are tested to verify their radiation hardness capability. The hardness assurance program at International Rectifier is comprised of two radiation environments. Every manufacturing lot is tested for total ionizing dose (per notes 5 and 6) using the TO-3 package. Both pre- and post-irradiation performance are tested and specified using the same drive circuitry and test conditions in order to provide a direct comparison.

Table 1. Electrical Characteristics @ Tj = 25°C, Post Total Dose Irradiation ⑤⑥

	Parameter	100K Rads (Si)		Units	Test Conditions ⑧
		Min	Max		
BV _{DSS}	Drain-to-Source Breakdown Voltage	200	—	V	V _{GS} = 0V, I _D = 1.0mA
V _{GS(th)}	Gate Threshold Voltage	2.0	4.5		V _{GS} = V _{DS} , I _D = 1.0mA
I _{GSS}	Gate-to-Source Leakage Forward	—	100	nA	V _{GS} = 20V
I _{GSS}	Gate-to-Source Leakage Reverse	—	-100		V _{GS} = -20V
I _{DSS}	Zero Gate Voltage Drain Current	—	10	μA	V _{DS} = 160V, V _{GS} = 0V
R _{DS(on)}	Static Drain-to-Source ④ On-State Resistance (TO-3)	—	0.222	Ω	V _{GS} = 12V, I _D = 4.5A
R _{DS(on)}	Static Drain-to-Source ④ On-State Resistance (TO-39)	—	0.24	Ω	V _{GS} = 12V, I _D = 4.5A
V _{SD}	Diode Forward Voltage ④	—	1.5	V	V _{GS} = 0V, I _D = 7.0A

International Rectifier radiation hardened MOSFETs have been characterized in heavy ion environment for Single Event Effects (SEE). Single Event Effects characterization is illustrated in Fig. a and Table 2.

Table 2. Single Event Effect Safe Operating Area

Ion	LET MeV/(mg/cm ²))	Energy (MeV)	Range (μm)	V _{DS} (V)				
				@V _{GS} =0V	@V _{GS} =-5V	@V _{GS} =-10V	@V _{GS} =-15V	@V _{GS} =-20V
Br	36.7	309	39.5	200	200	200	200	200
I	59.8	341	32.5	200	200	200	185	120
Au	82.3	350	28.4	200	200	150	50	25

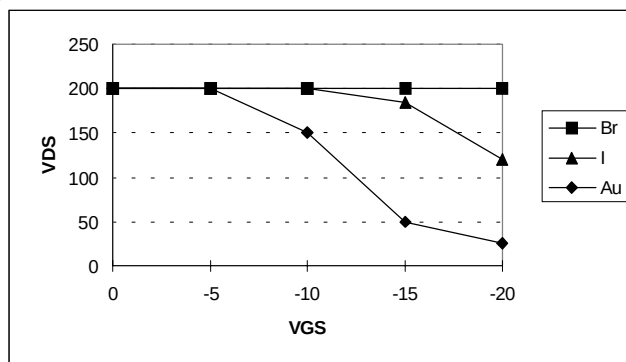


Fig a. Single Event Effect, Safe Operating Area

For footnotes refer to the last page

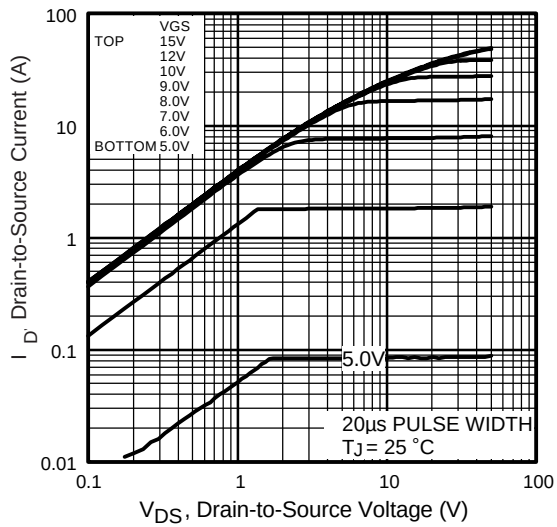


Fig 1. Typical Output Characteristics

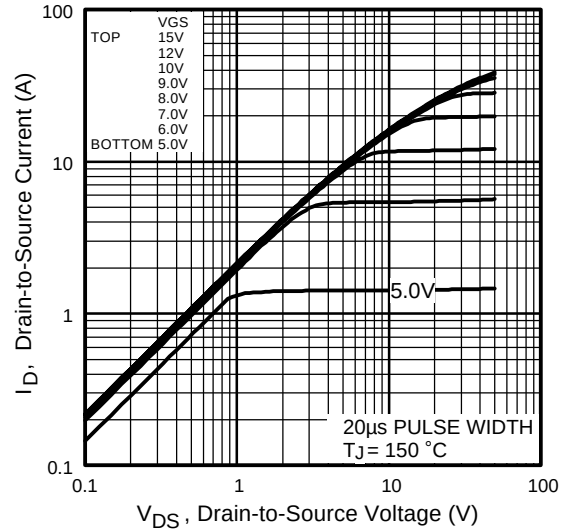


Fig 2. Typical Output Characteristics

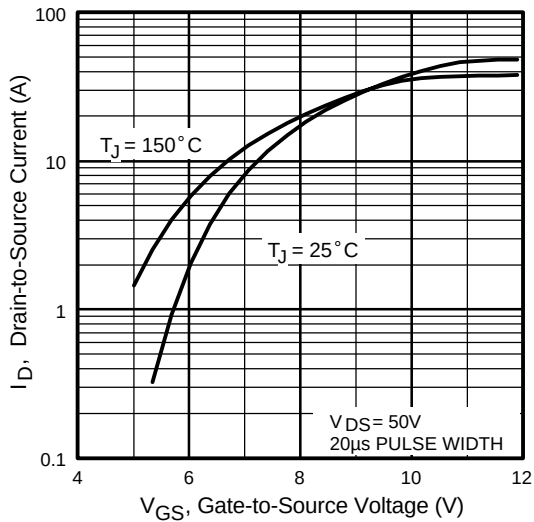
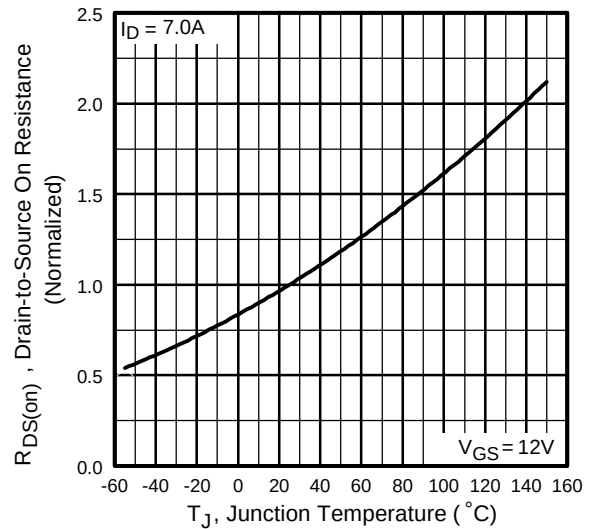


Fig 3. Typical Transfer Characteristics

Fig 4. Normalized On-Resistance
Vs. Temperature

Pre-Irradiation

IRHF57230SE, JANSR2N7498T2

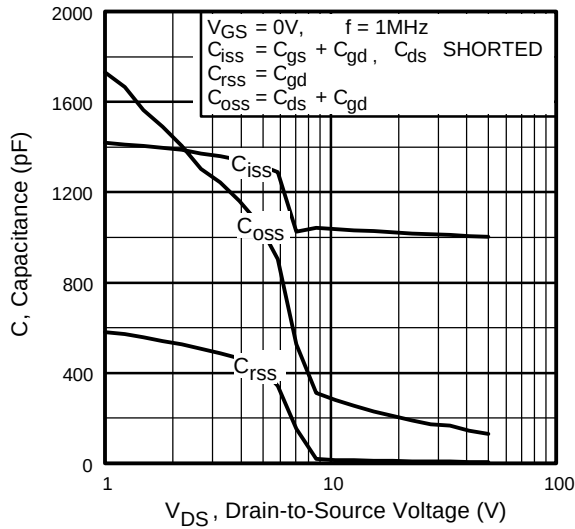


Fig 5. Typical Capacitance Vs. Drain-to-Source Voltage

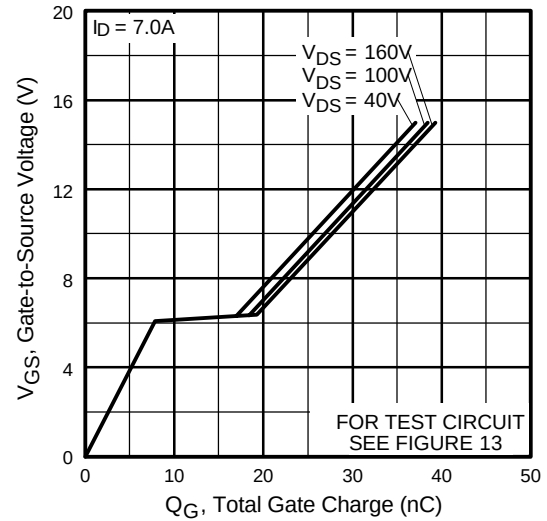


Fig 6. Typical Gate Charge Vs. Gate-to-Source Voltage

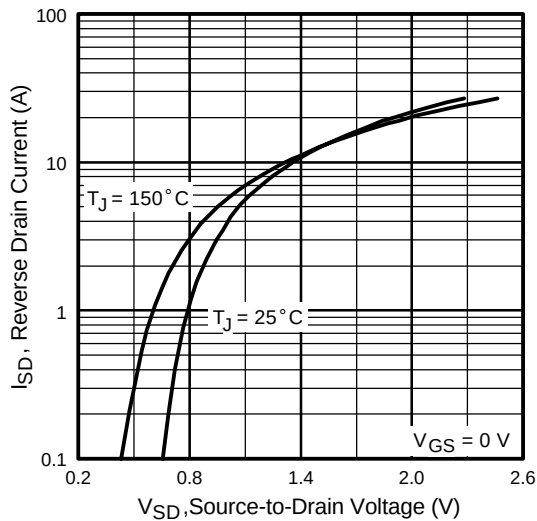


Fig 7. Typical Source-Drain Diode Forward Voltage

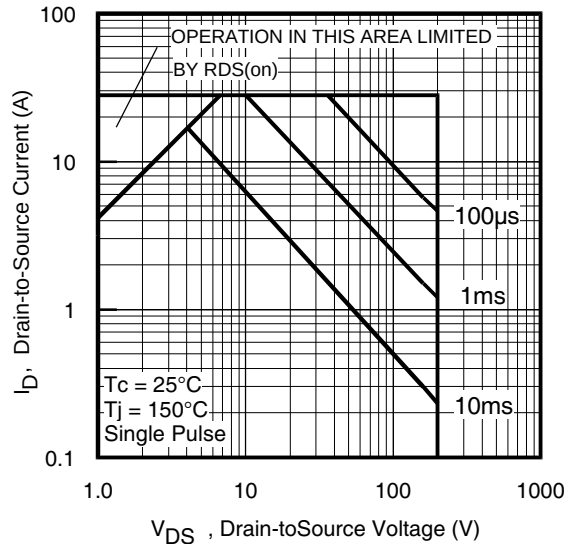


Fig 8. Maximum Safe Operating Area

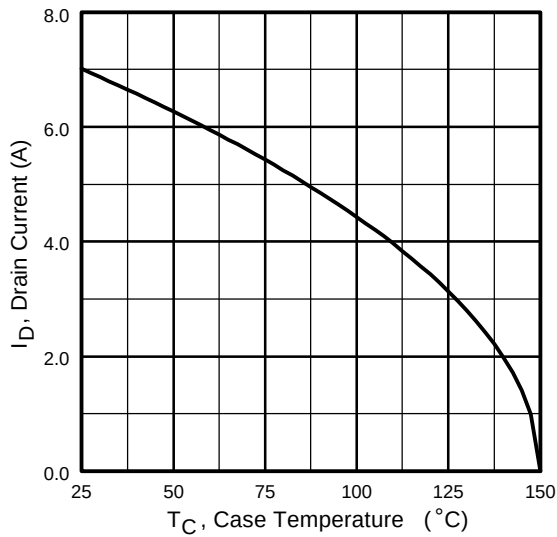


Fig 9. Maximum Drain Current Vs. Case Temperature

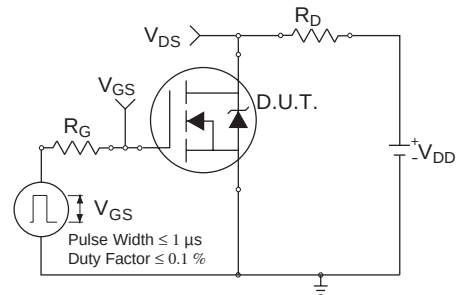


Fig 10a. Switching Time Test Circuit

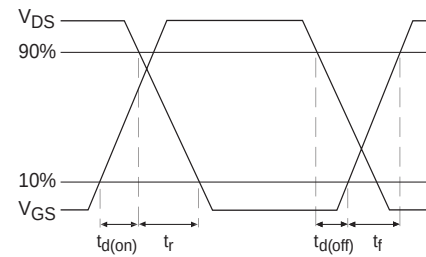


Fig 10b. Switching Time Waveforms

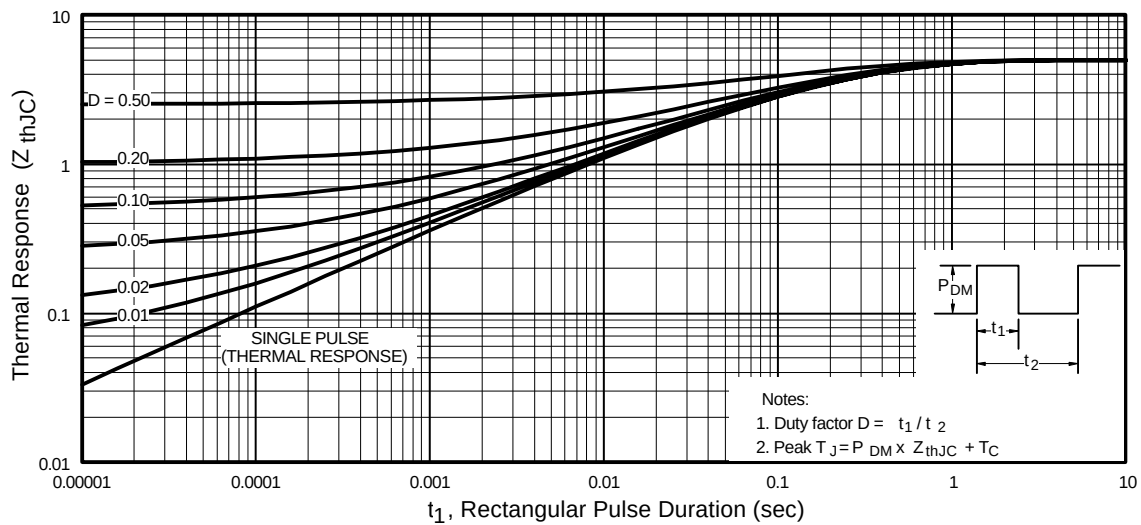


Fig 11. Maximum Effective Transient Thermal Impedance, Junction-to-Case

Pre-Irradiation

IRHF57230SE, JANSR2N7498T2

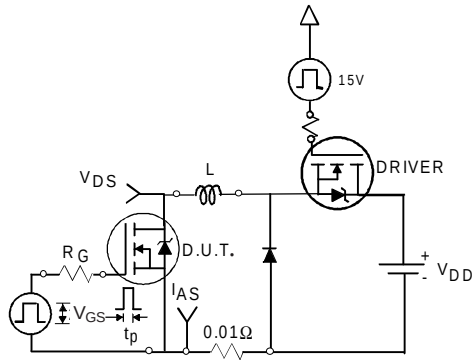


Fig 12a. Unclamped Inductive Test Circuit

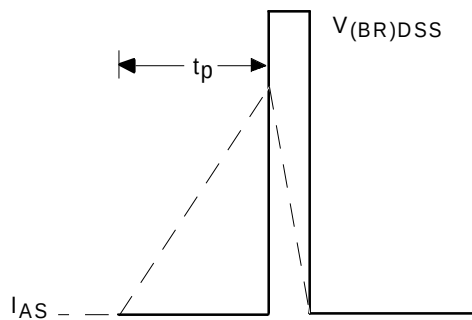


Fig 12b. Unclamped Inductive Waveforms

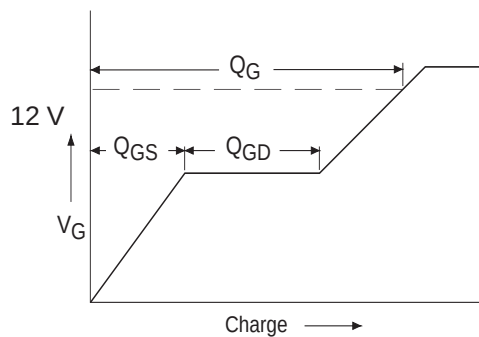


Fig 13a. Basic Gate Charge Waveform

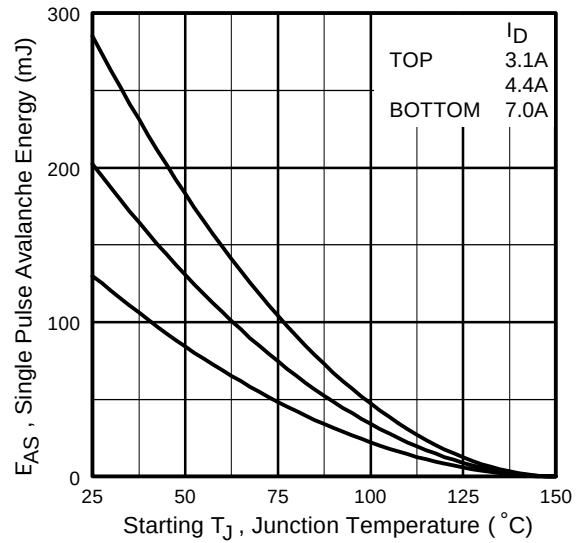


Fig 12c. Maximum Avalanche Energy Vs. Drain Current

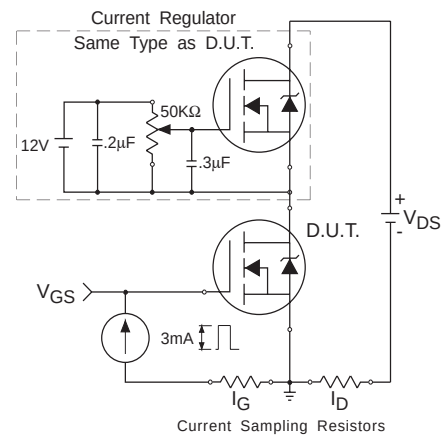


Fig 13b. Gate Charge Test Circuit

